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(54) **METHOD OF MANUFACTURING AN INTEGRATED DEVICE COMPISING ANODIC POROUS OXIDE WITH LIMITED ROUGHNESS**

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(57) **ABSTRACT**

A method of manufacturing an integrated device that includes: forming, on a substrate, a metal anodization barrier layer; planarizing the metal anodization barrier layer; forming, on the planarized metal anodization barrier layer, an anodizable metal layer; planarizing the anodizable metal layer; and anodizing the planarized anodizable metal layer to obtain an anodic porous oxide region having a plurality of substantially straight pores that extend from a top surface of the anodic porous oxide region towards the metal anodization barrier layer.

